

HiPerFRED

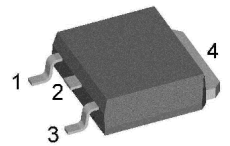
V_{RRM}	=	300 V
I_{FAV}	=	10 A
t_{rr}	=	35 ns

High Performance Fast Recovery Diode
Low Loss and Soft Recovery
Single Diode

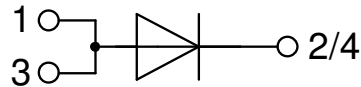
Part number

DPG10IM300UC

Marking on Product: PAOGUI



Backside: cathode



Features / Advantages:

- Planar passivated chips
- Very low leakage current
- Very short recovery time
- Improved thermal behaviour
- Very low I_{rm} -values
- Very soft recovery behaviour
- Avalanche voltage rated for reliable operation
- Soft reverse recovery for low EMI/RFI
- Low I_{rm} reduces:
 - Power dissipation within the diode
 - Turn-on loss in the commutating switch

Applications:

- Antiparallel diode for high frequency switching devices
- Antisaturation diode
- Snubber diode
- Free wheeling diode
- Rectifiers in switch mode power supplies (SMPS)
- Uninterruptible power supplies (UPS)

Package: TO-252 (DPak)

- Industry standard outline
- RoHS compliant
- Epoxy meets UL 94V-0

Terms Conditions of usage:

The data contained in this product data sheet is exclusively intended for technically trained staff. The user will have to evaluate the suitability of the product for the intended application and the completeness of the product data with respect to his application. The specifications of our components may not be considered as an assurance of component characteristics. The information in the valid application- and assembly notes must be considered. Should you require product information in excess of the data given in this product data sheet or which concerns the specific application of your product, please contact the sales office, which is responsible for you.

Due to technical requirements our product may contain dangerous substances. For information on the types in question please contact the sales office, which is responsible for you.

Should you intend to use the product in aviation, in health or life endangering or life support applications, please notify. For any such application we urgently recommend

- to perform joint risk and quality assessments;

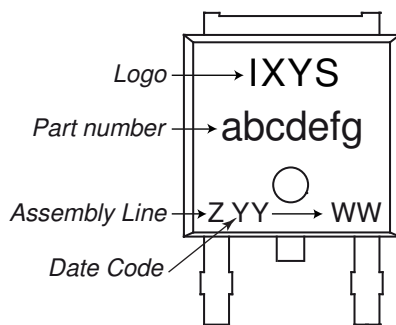
- the conclusion of quality agreements;

- to establish joint measures of an ongoing product survey, and that we may make delivery dependent on the realization of any such measures.

Fast Diode				Ratings			
Symbol	Definition	Conditions		min.	typ.	max.	Unit
V_{RSM}	max. non-repetitive reverse blocking voltage					300	V
V_{RRM}	max. repetitive reverse blocking voltage					300	V
I_R	reverse current, drain current	$V_R = 300\text{ V}$		$T_{VJ} = 25^\circ\text{C}$		1	μA
		$V_R = 300\text{ V}$		$T_{VJ} = 150^\circ\text{C}$		0.06	mA
V_F	forward voltage drop	$I_F = 10\text{ A}$		$T_{VJ} = 25^\circ\text{C}$		1.27	V
		$I_F = 20\text{ A}$				1.45	V
		$I_F = 10\text{ A}$		$T_{VJ} = 150^\circ\text{C}$		0.98	V
		$I_F = 20\text{ A}$				1.17	V
I_{FAV}	average forward current	$T_C = 150^\circ\text{C}$	rectangular	$T_{VJ} = 175^\circ\text{C}$		10	A
V_{FO}	threshold voltage			$T_{VJ} = 175^\circ\text{C}$		0.74	V
r_F	slope resistance					17.7	m Ω
R_{thJC}	thermal resistance junction to case					2.3	K/W
R_{thCH}	thermal resistance case to heatsink				0.50		K/W
P_{tot}	total power dissipation			$T_C = 25^\circ\text{C}$		65	W
I_{FSM}	max. forward surge current	$t = 10\text{ ms}; (50\text{ Hz}), \text{ sine}; V_R = 0\text{ V}$		$T_{VJ} = 45^\circ\text{C}$		140	A
C_J	junction capacitance	$V_R = 150\text{ V}$ $f = 1\text{ MHz}$		$T_{VJ} = 25^\circ\text{C}$		15	pF
I_{RM}	max. reverse recovery current			$T_{VJ} = 25^\circ\text{C}$		3	A
t_{rr}	reverse recovery time			$T_{VJ} = 125^\circ\text{C}$		5.5	A
				$T_{VJ} = 25^\circ\text{C}$		35	ns
				$T_{VJ} = 125^\circ\text{C}$		45	ns

Package TO-252 (DPak)			Ratings			
Symbol	Definition	Conditions	min.	typ.	max.	Unit
I_{RMS}	RMS current	per terminal ¹⁾			20	A
T_{VJ}	virtual junction temperature		-55		175	°C
T_{op}	operation temperature		-55		150	°C
T_{stg}	storage temperature		-55		150	°C
Weight				0.3		g
F_C	mounting force with clip		20		60	N

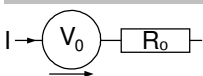
¹⁾ I_{RMS} is typically limited by the pin-to-chip resistance (1); or by the current capability of the chip (2). In case of (1) and a product with multiple pins for one chip-potential, the current capability can be increased by connecting the pins as one contact.

Product Marking

Part description

- D = Diode
- P = HiPerFRED
- G = extreme fast
- 10 = Current Rating [A]
- IM = Single Diode
- 300 = Reverse Voltage [V]
- UC = TO-252AA (DPak)

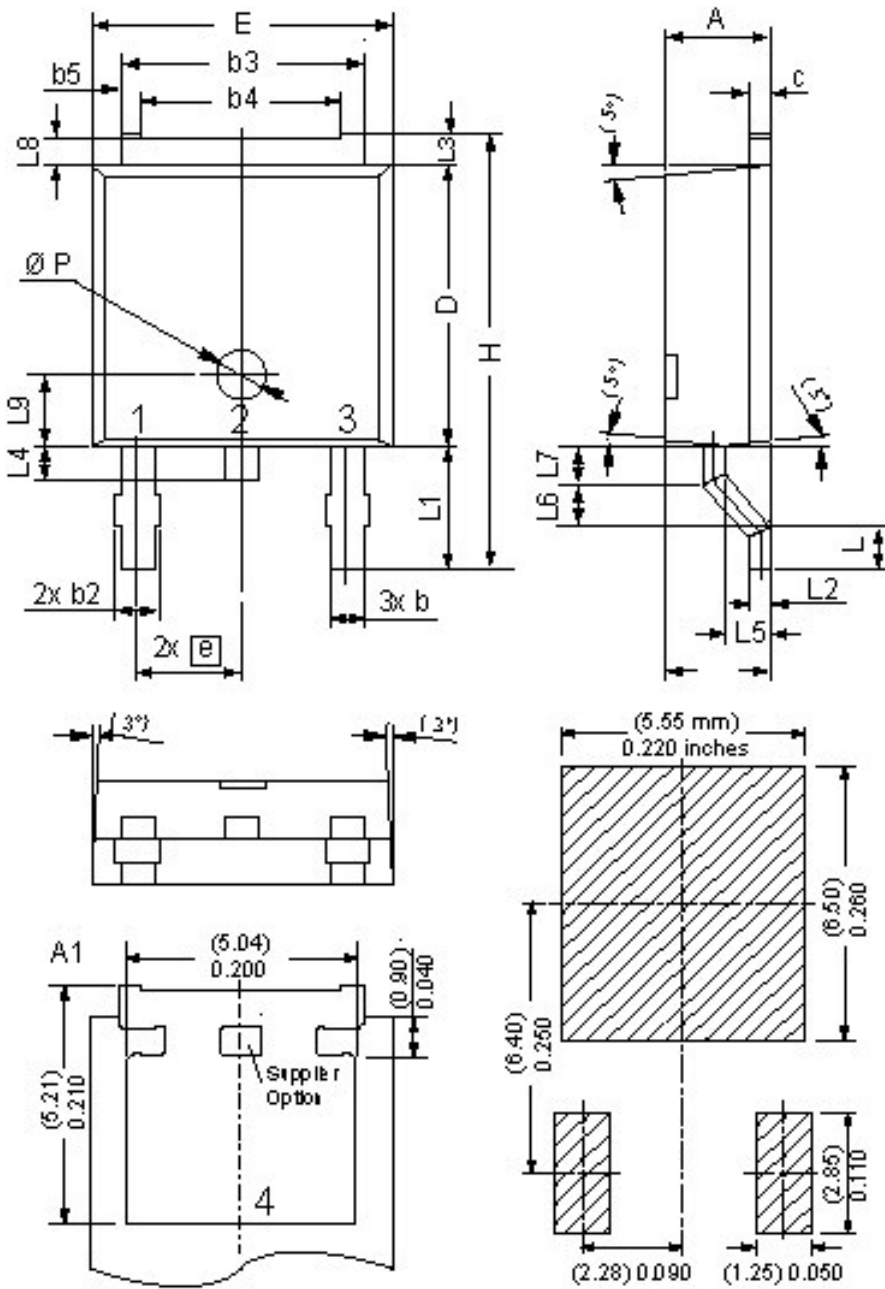
Ordering	Ordering Number	Marking on Product	Delivery Mode	Quantity	Code No.
Standard	DPG10IM300UC	PAOGUI	Tape & Reel	2500	505682

Similar Part	Package	Voltage class
DPG10I300PA	TO-220AC (2)	300

Equivalent Circuits for Simulation
** on die level*
 $T_{VJ} = 175\text{ °C}$

Fast Diode

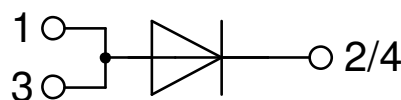
$V_{0\ max}$	threshold voltage	0.74	V
$R_{0\ max}$	slope resistance *	14.5	mΩ

Outlines TO-252 (DPak)



Dim	Millimeters		Inches	
	min	max	min	max
A	2.20	2.40	0.087	0.094
A1	2.10	2.50	0.083	0.098
b	0.66	0.86	0.026	0.034
b2	-	0.96	-	0.038
b3	5.04	5.64	0.198	0.222
b4	4.34 BSC		0.171 BSC	
b5	0.50 BSC		0.020 BSC	
c	0.40	0.86	0.016	0.034
D	5.90	6.30	0.232	0.248
E	6.40	6.80	0.252	0.268
e	2.10	2.50	0.083	0.098
H	9.20	10.10	0.362	0.398
L	0.55	1.28	0.022	0.050
L1	2.50	2.90	0.098	0.114
L2	0.40	0.60	0.016	0.024
L3	0.50	0.90	0.020	0.035
L4	0.60	1.00	0.024	0.039
L5	0.82	1.22	0.032	0.048
L6	0.79	0.99	0.031	0.039
L7	0.81	1.01	0.032	0.040
L8	0.40	0.80	0.016	0.031
L9	1.50 BSC		0.059 BSC	
Ø P	1.00 BSC		0.039 BSC	

Recommended min. foot print



Fast Diode

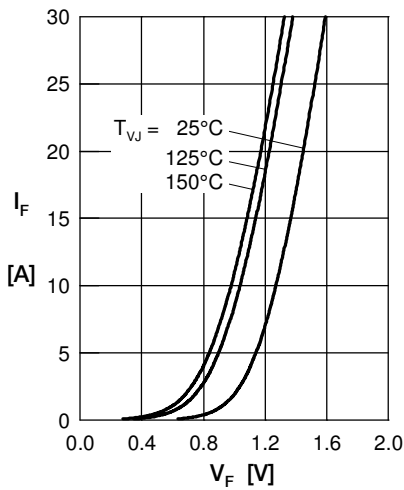


Fig. 1 Forward current I_F versus V_F

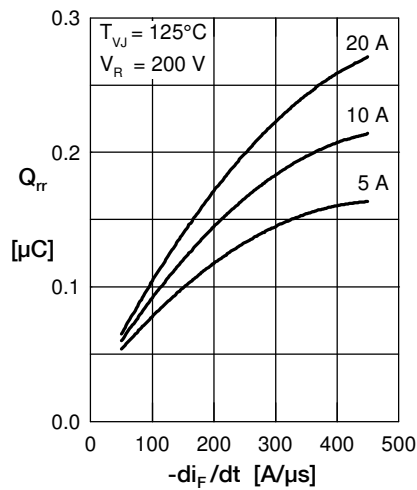


Fig. 2 Typ. reverse recov. charge Q_{rr} versus $-di_F/dt$

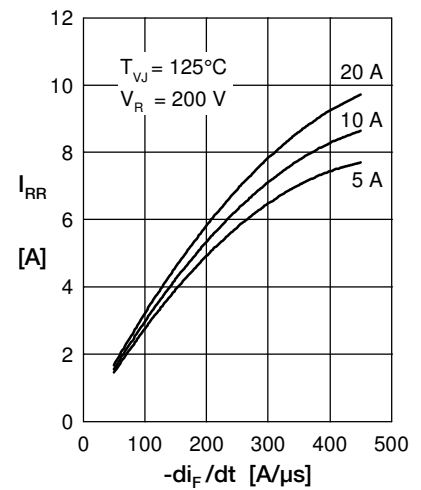


Fig. 3 Typ. reverse recov. current I_{RR} versus $-di_F/dt$

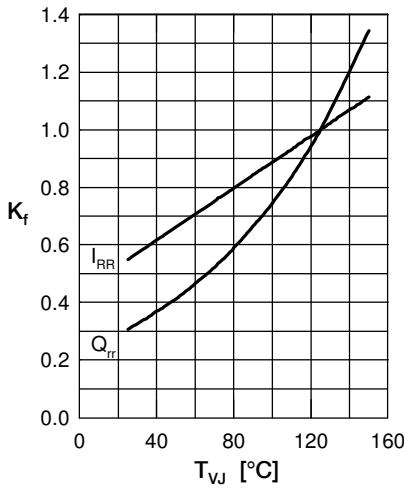


Fig. 4 Typ. dynamic parameters Q_{rr} , I_{RR} versus T_{VJ}

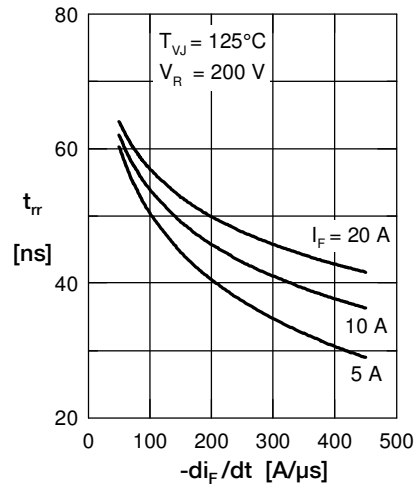


Fig. 5 Typ. reverse recov. time t_{rr} versus $-di_F/dt$

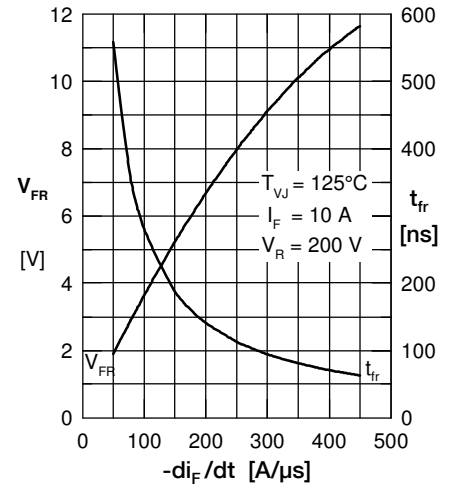


Fig. 6 Typ. forward recov. voltage V_{FR} and t_{fr} versus di_F/dt

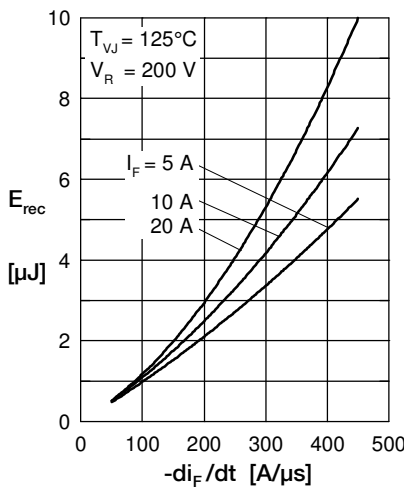


Fig. 7 Typ. recovery energy E_{rec} versus $-di_F/dt$

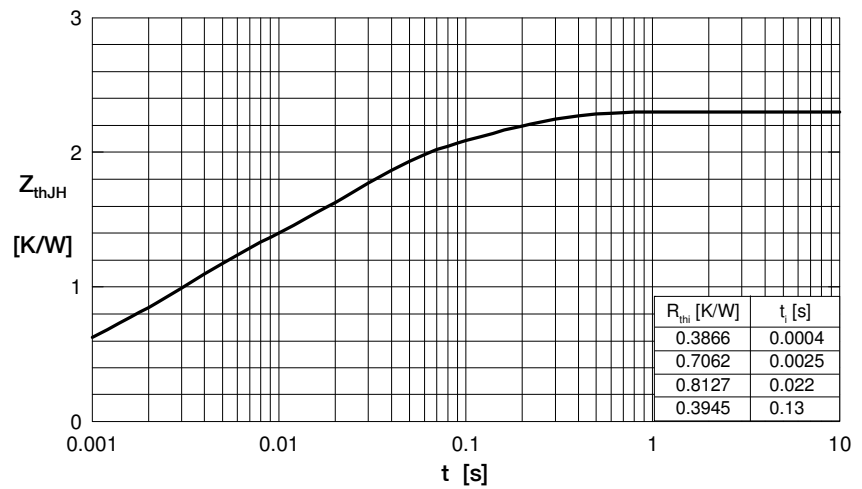


Fig. 8 Transient thermal resistance junction to case